



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



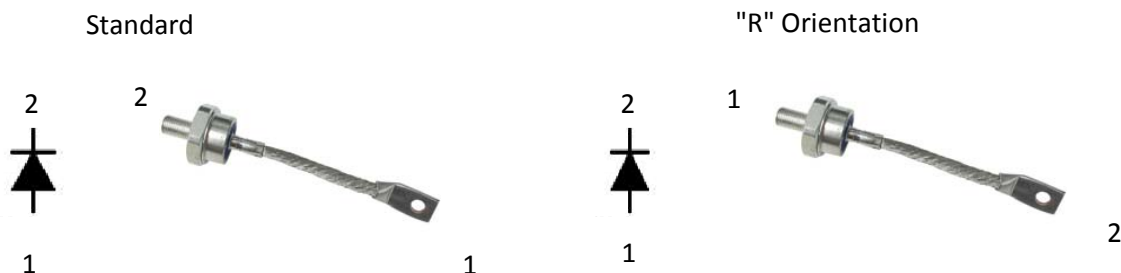
Silicon Standard Recovery Diode

$V_{RRM} = 200 \text{ V} - 1400 \text{ V}$
 $I_F = 100 \text{ A}$

Features

- High Surge Capability
- Types up to 1400 V V_{RRM}

DO-8 Package



Maximum ratings, at $T_j = 25^\circ\text{C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	1N3289A(R)	1N3291A(R)	1N3293A(R)	1N3294A(R)	Unit
Repetitive peak reverse voltage	V_{RRM}		200	400	600	800	V
DC blocking voltage	V_{DC}		200	400	600	800	V
Continuous forward current	I_F	$T_C \leq 130^\circ\text{C}$	100	100	100	100	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25^\circ\text{C}$, $t_p = 8.3 \text{ ms}$	2300	2300	2300	2300	A
I_2t for fusing	I_2t	60 Hz Half wave	22000	22000	22000	22000	A^2sec
Operating temperature	T_j		-40 to 200	-40 to 200	-40 to 200	-40 to 200	$^\circ\text{C}$
Storage temperature	T_{stg}		-40 to 200	-40 to 200	-40 to 200	-40 to 200	$^\circ\text{C}$

Electrical characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	1N3289A(R)	1N3291A(R)	1N3293A(R)	1N3294A(R)	Unit
Diode forward voltage	V_F	$I_F = 100 \text{ A}$, $T_j = 130^\circ\text{C}$	1.5	1.5	1.5	1.5	V
Reverse current	I_R	$V_R = V_{RRM}$, $T_j = 130^\circ\text{C}$	24	24	17	13	mA

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		0.40	0.40	0.40	0.40	$^\circ\text{C/W}$
-------------------------------------	------------	--	------	------	------	------	--------------------

Electrical Characteristics

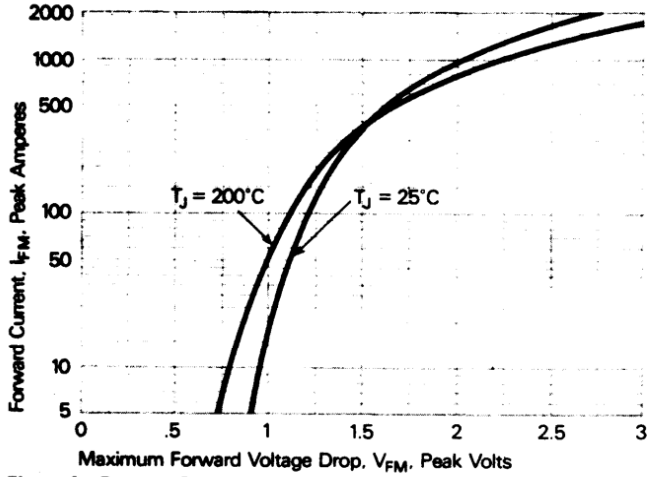


Figure 1. Forward Current vs. Forward Voltage.

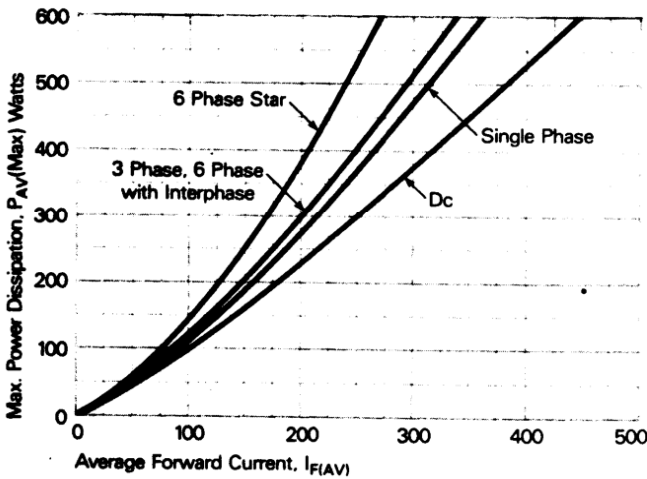


Figure 3. Power dissipation vs. Average forward current.

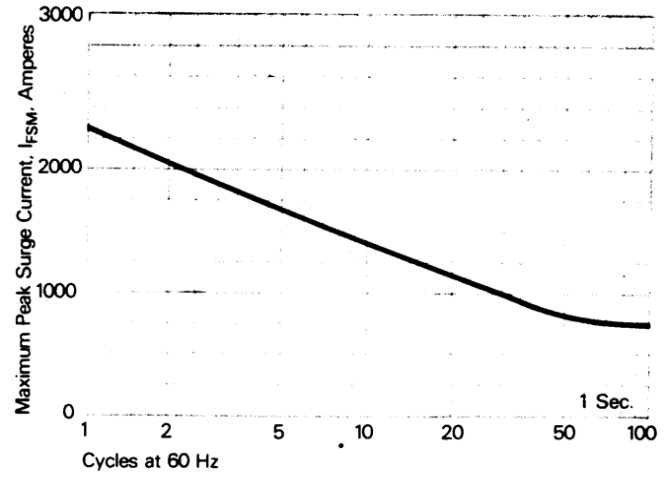


Figure 2. Maximum allowable surge current at rated load conditions.

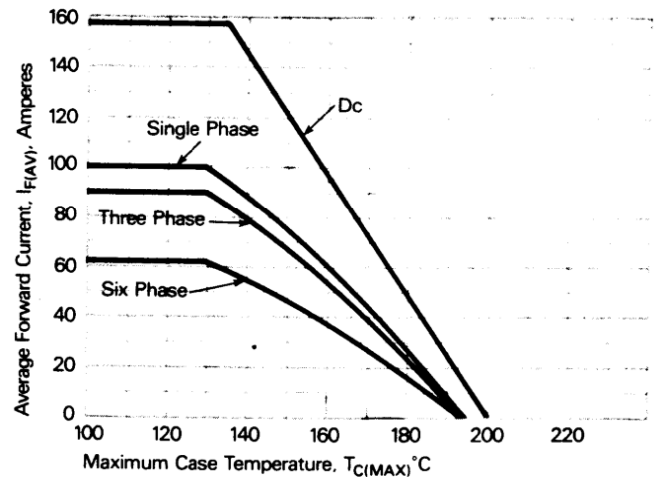


Figure 4. Forward Current vs. Case Temperature.